

# HCAL heat dissipation and power management

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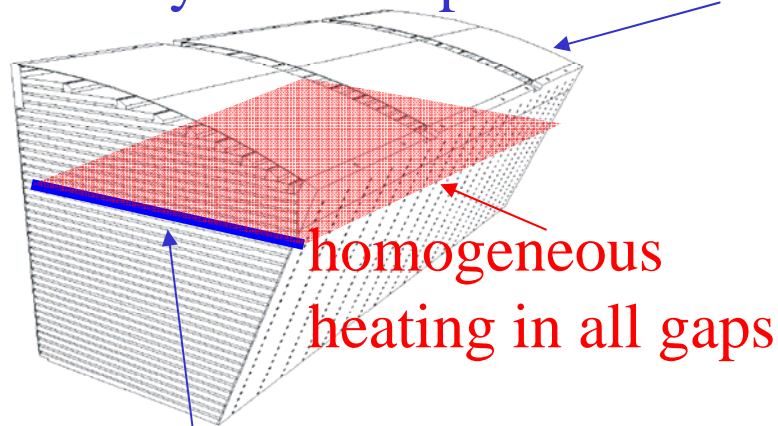
Rough ideas, calculations and numbers

What is easy?      Where are problems?

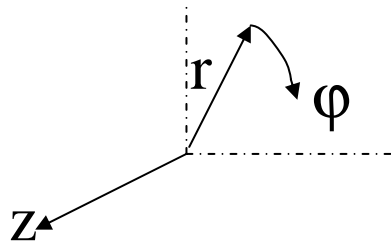
- Heat transfer
- Charge storage for pulsed operation

# Heat transfer

symmetry: no transport at  $z=0\text{m}$



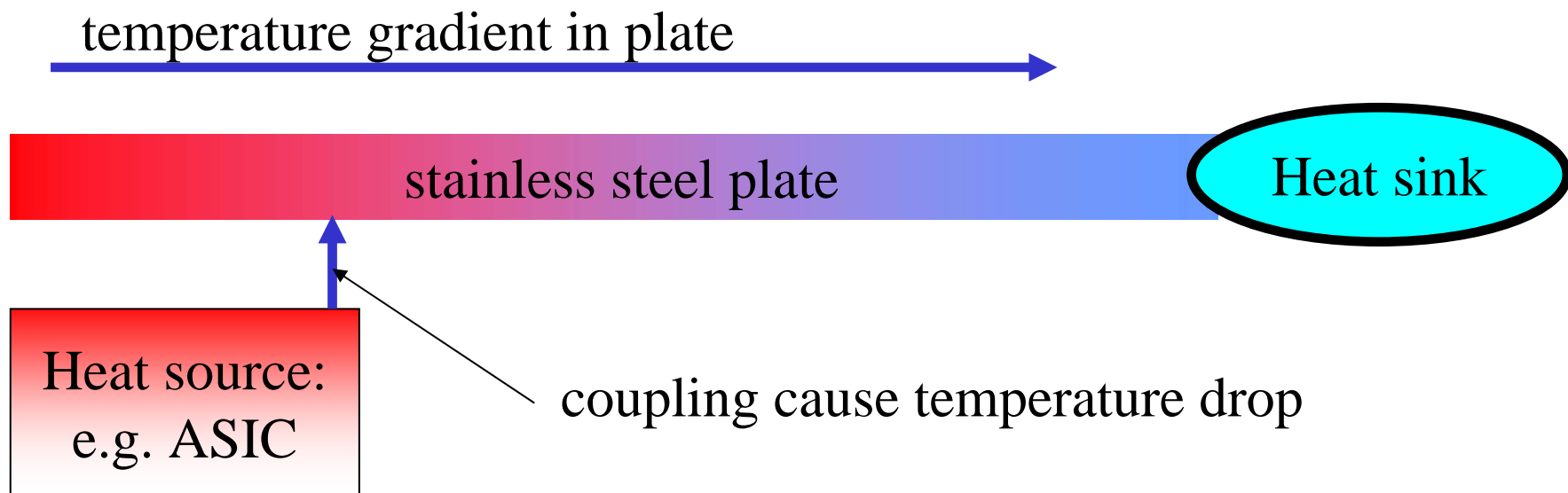
cooling at the ends:  $z=\pm 2.2\text{m}$



Heat transport in directions:

- $\varphi$  homogeneous heating:  
    ➔ No heat transfer in  $\varphi$
- $r$  alternating structure  
    with air gaps  
    every air gap is heating  
    ➔ No heat transfer in  $r$
- $z$  cooling at end plate  
    Heat flows in solid material,  
    air gaps too small, no convection

# Heat transfer



# Heat transfer in steel plate: Basic parameters

## Heat production:

Power:  $P_{\text{chan}} = 40 \mu\text{W}/\text{chan}$

ASIC:  $25 \mu\text{W}/\text{chan}$

HV:  $+15 \mu\text{W}/\text{chan}$ :  $50\text{V} * 0.3 \mu\text{A}$

Infrastructure: + ??

## Geometry:

$N_{\text{chan}} = 1000/\text{m}^2$

$D_{\text{steel}} = 2\text{cm}$  (thickness)

$L_{\text{heat}} = 2.2\text{m}$  (length)

## Material constants:

Stainless steel: Which one?

$\lambda_{\text{steel}} = 15\text{W}/\text{Km}$  other publication 15-25W/Km

$K_{\text{steel}} = 3.7\text{MJ}/\text{m}^3\text{K}$

# Easier geometry: One direction "z" for transport

## Energy conservation:

$$\text{energy in "dz"} = \text{heat flow inside steel} + \text{heat from electronic}$$

$$\kappa dVolume \frac{\partial T}{\partial t} = -dArea_{transvers} \frac{\partial \Delta Q_{out-in}}{\partial t} + P_{chan} N_{chan} dArea_{heating}$$

## Heat transport:

$$\frac{\partial Q}{\partial t} = -\lambda_{steel} Area_{transverse} \frac{\partial T}{\partial z}$$

$$\kappa_{steel} d_{steel} \frac{\partial T}{\partial t} = \lambda_{steel} d_{steel} \frac{\partial^2 T}{\partial z^2} + P_{chan} N_{chan}$$

# Solution after long heating

Long heating:  $\frac{\partial T}{\partial t} = 0$

No heat transport at  $z=0$  (Symmetry point)

$$T = -(z^2 - L_{heat}^2) \frac{P_{chan} N_{chan}}{2\lambda_{steel} d_{steel}}$$

For  $L_{heat}=2.2\text{m}$  the temperature raise at  $z=0\text{m}$ :  $T(0\text{m}) = 0.33\text{K}$

Every thing is from formula, so it is easy to adapt, when getting more accurate information: tile-size, power,....

**OK, but keep end well cooled!!!!!!**

**and take care to add not many more heat sources !!!!**

# Time dependence

Fourier transformation with components parameterized by  $\tau$ ,  $\alpha(\tau)$

elements:  $A e^{-(t/\tau)} \cos(2\pi \alpha (x/L_{\text{heat}}))$

$\alpha$  is part of the wavelength inside the steel plate

One cooled end, and one with to heat flow:  $\alpha = (1/4, 3/4, 5/4, \dots)$

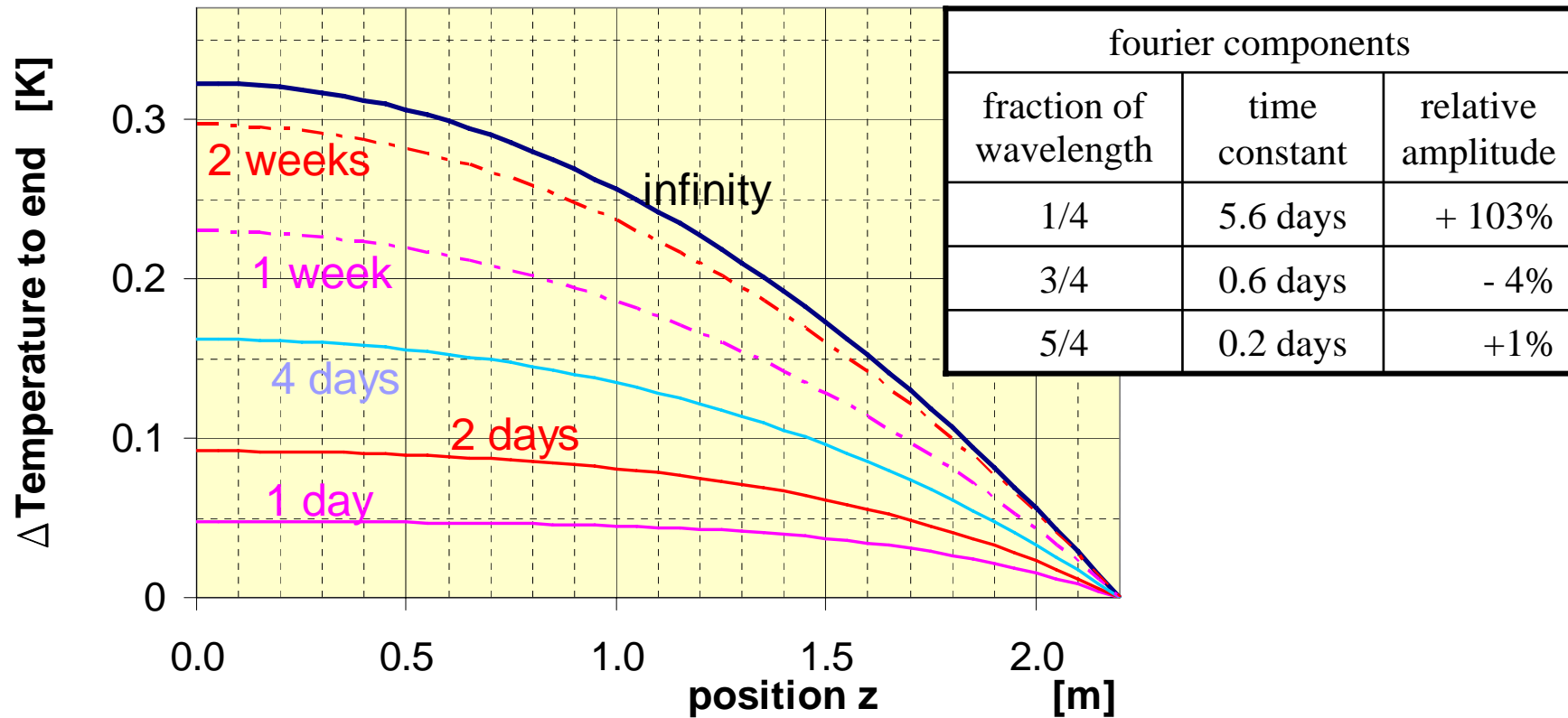
$$\tau = \frac{\kappa_{\text{steel}} L_{\text{heat}}^2}{4\pi^2 \lambda_{\text{steel}} \alpha^2}$$

Slowest component ( $\alpha=1/4$ ) :

$$\tau = 5.6 \text{ days}$$

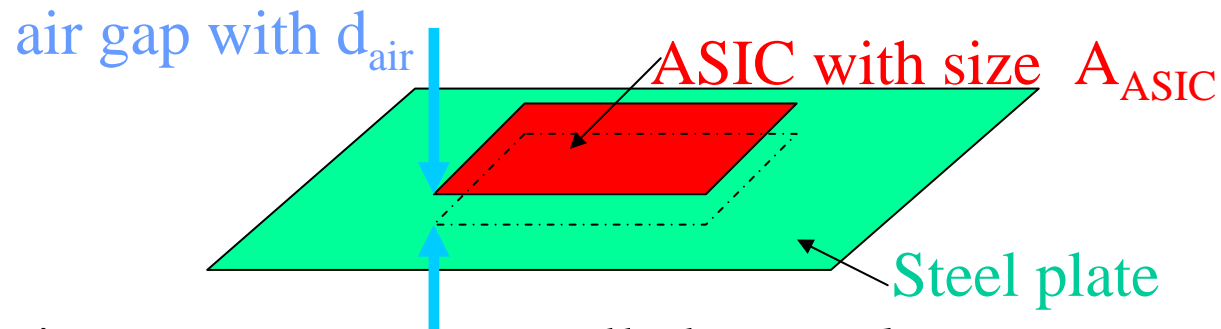
# Heating HCAL

## Heating up of HCAL





# Heat transfer: ASIC to steel



Basic parameters: *not really known, but to get a guess:*

$$\lambda_{air} = 24 \text{ mW/Km (Nitrogen)}$$

$$A_{ASIC} = 4 \text{ cm}^2$$

$$d_{air} = 1 \text{ mm}$$

$$P_{ASIC} = (64 \text{ channel}) * P_{chan} = 1.6 \text{ mW}$$

Temperature difference at air gap:  
without convection (small gap)

$$\Delta T_{gap} = \frac{1}{\lambda_{air}} P_{ASIC} \frac{d_{air}}{A_{ASIC}}$$

$$\rightarrow \Delta T_{gap} = 0.2 \text{ K} \quad \text{OK!!!!!!}$$

# Charge storage for pulsed operation

## Boundary conditions:

Bunch train of 0.6ms every 200ms:

- power down the "hungry" electronics
- store enough charge locally, to reduce cables out of ILC-detector and EMI-problems

⇒ Store the charge at the end of the gap on data concentrator

- minimize components and heating inside the gap

## Basic parameters:

$$P_{\text{chan}} = 25 \mu\text{W/channel (ASIC)}$$

$$N_{\text{chan}} = 1000/\text{m}^2$$

$$A_{\text{plane}} = 2\text{m}^2 \text{ (typically)}$$

$$R_{\text{train}} = 5\text{Hz (repetition rate)}$$

$$T_{\text{train}} = 1\text{ms (switch on time)}$$

$$V_{\text{pulsed}} = 3.3\text{V (operation voltage of ASIC)}$$

# Required charge / current

Charge for train:

$$Q_{train} = \frac{P_{chan}}{V_{pulsed} R_{train}} N_{chan} A_{plane} = 3\text{mC}/(\text{train plane})$$

Current during train:

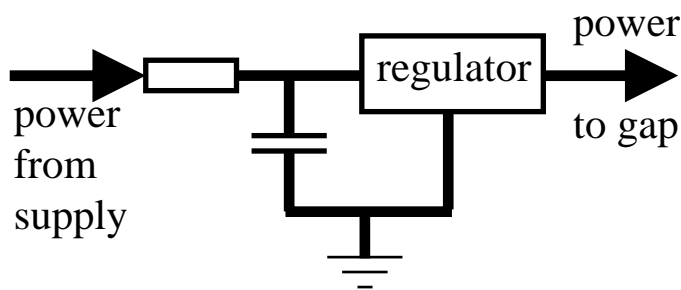
$$I_{train} = \frac{Q_{train}}{T_{train}} = 3\text{A}/\text{plane}$$

➔ Values do not look critical,  
but to be handled with a some effort

# Straight forward solution

**Idea:** Store the charge at end of the gap in data concentrator  
 put a voltage regulator before the current enters the gap  
 avoid fast current jumps on the cables to power supply

**Available capacitors:**



Capacitance [Farad]	10 <sup>-6</sup>	10 <sup>-4</sup>	10 <sup>-2</sup>	10 <sup>0</sup>	10 <sup>2</sup>	10 <sup>4</sup>	10 <sup>6</sup>
Aluminum electrolytic capacitor			→				
from Panasonic				←			
Gold capacitor				←	→		
Secondary battery cell						←	

$3.3\text{mF} = 7 \cdot 470\mu\text{F}$

**7 capacitors á 470 $\mu\text{F}$  (7.3mm\*4.3mm\*4.5mm) are sufficient**

discharge voltage drop 0.5V , so additional heat is small

Stored local energy is small: 0.2J/plane , no risk of fire

**Lots of details and other concepts to be evaluated**

# Power: Just first step, What else?

Lots of details and other concepts to be evaluated

Not touched at all:

- Waves inside Power-GND system  
Large planes:  $2.2\text{m} \times 1\text{m}$ :  
 $\lambda = 2.2\text{m}$  is equivalent to  $\nu = 90\text{MHz}$
- Current transfer inside the gap
- What is needed locally at ASIC?  
Is ASIC/SiPM/PCB sensitive?
- Regulator for fast reaction

⇒ Lot of work inside that work package

# Outlook

## Heating:

- Active electronics in the gap is no heat problem  
but keep eyes open for updates on power, pad size,
- Heat flows to end of gap, where it has to be cooled

## Power for pulsed operation:

- energy storage for pulsed operation is feasible  
Not touched: Lot of items

It looks promising for going ahead

Lot of work will be needed for details